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(71) Applicants (for all designated States except US):
CENTRE NATIONAL DE LA RECHERCHE SCIENTIFIQUE (CNRS) [FR/FR]; 3, rue Michel Ange,
F-75794 Paris Cedex 16 (FR). **ECOLE POLYTECHNIQUE** [FR/FR]; Route de Saclay, F-91128 Palaiseau
Cedex (FR).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **ROCA I CABAR-ROCAS, Pere** [ES/FR]; 13bis, rue Girardot, F-91140
Villebon sur Yvette (FR). **VANDERHAGHEN, Régis**
[FR/FR]; 49, rue du Moulin, F-92120 Palaiseau (FR).
DREVILLON, Bernard [FR/FR]; 15, Cité de la Pépinière,
F-92140 Clamart (FR).

(74) Agents: **MICHELET, Alain et al.**; Cabinet Harlé et
Phélip, 7, rue de Madrid, F-75008 Paris (FR).

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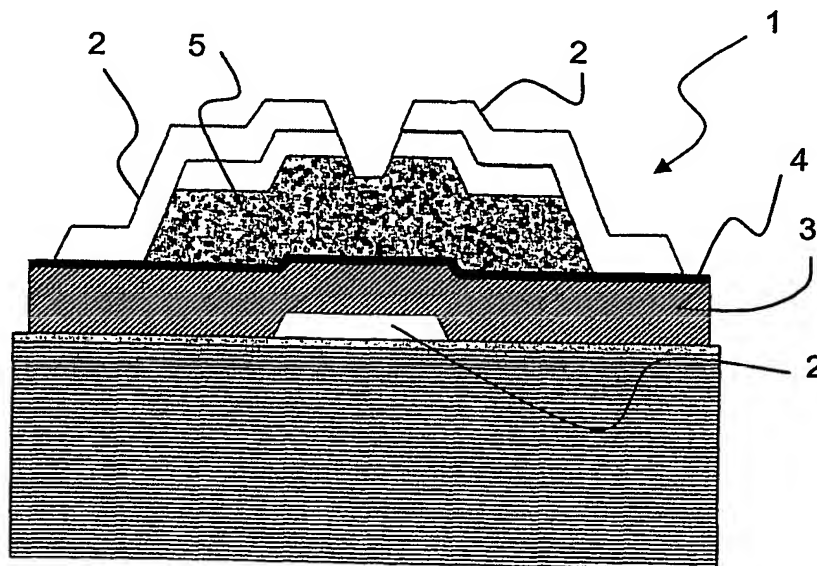
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(54) Title: TRANSISTOR FOR ACTIVE MATRIX DISPLAY AND A METHOD FOR PRODUCING SAID TRANSISTOR



(57) Abstract: The invention concerns a transistor for active matrix display and a method for producing the said transistor (1). The transistor (1) comprises a microcrystalline silicon film (5) and an insulator (3). The crystalline fraction of the said microcrystalline silicon film (5) is above 80%. According to the invention, the transistor (1) comprises a plasma treated interface (4) located between the insulator (3) and the microcrystalline silicon film (5) so that the said transistor (1) has a linear mobility equal or superior to 1.5 cm²V⁻¹s⁻¹, shows threshold voltage stability and wherein the microcrystalline silicon film (5) comprises grains (6) whose size ranges between 10 nm and 400 nm. The invention concerns as well a display unit having a line-column matrix of pixels that are actively addressed, each pixel comprising at least a transistor

as described above.

WO 2004/070848 A1